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# HRU0203A

Silicon Schottky Barrier Diode for Rectifying

# HITACHI

ADE-208-469A (Z)

Rev 1

November 1996

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## Features

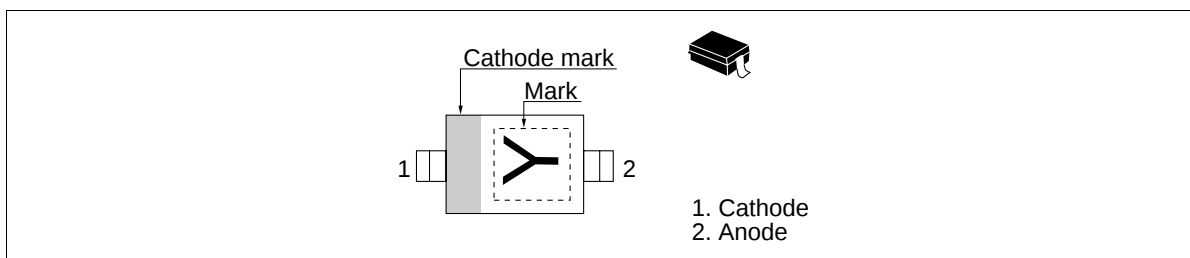
- Low forward voltage drop and suitable for high efficiency forward current.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

## Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HRU0203A | Y          | URP          |

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## Outline



## HRU0203A

### Absolute Maximum Ratings (Ta = 25°C)

| Item                                      | Symbol | Value    | Unit |
|-------------------------------------------|--------|----------|------|
| Repetitive peak reverse voltage           | VRRM*1 | 30       | V    |
| Average rectified current                 | Io*2   | 200      | mA   |
| Non-Repetitive peak forward surge current | IFSM*3 | 2        | A    |
| Junction temperature                      | Tj     | 125      | °C   |
| Storage temperature                       | Tstg   | -55~+125 | °C   |

Note 1. See Fig.3

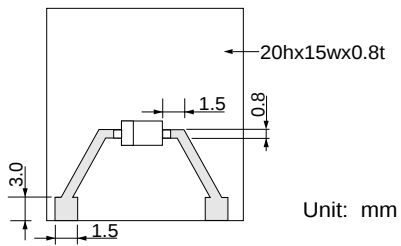
Note 2. See Fig.4

Note 3. 10msec sine wave 1 pulse

### Electrical Characteristics (Ta = 25°C)

| Item               | Symbol   | Min | Typ | Max  | Unit | Test Condition        |
|--------------------|----------|-----|-----|------|------|-----------------------|
| Forward voltage    | VF       | ~   | ~   | 0.50 | V    | IF = 200 mA           |
| Reverse current    | IR       | ~   | ~   | 50   | μA   | VR = 30V              |
| Thermal resistance | Rth(j-a) | ~   | 520 | ~    | °C/W | Polyimide substrate*1 |

Note 1. Polyimide PCB



## Main Characteristic

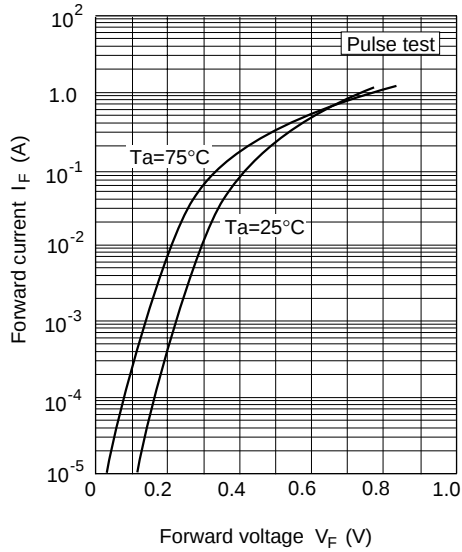


Fig.1 Forward current Vs. Forward voltage

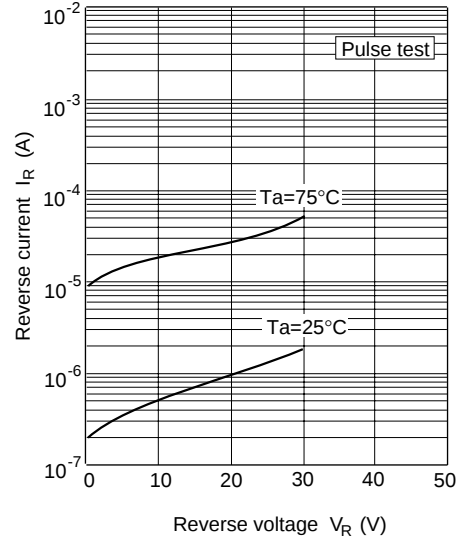


Fig.2 Reverse current Vs. Reverse voltage

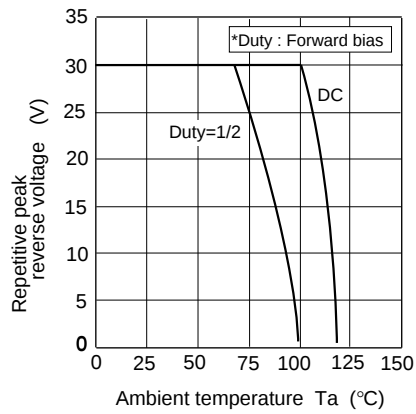


Fig.3 Repetitive peak reverse voltage Vs. Ambient temperature

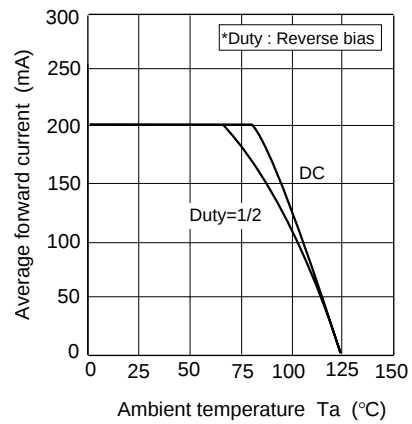


Fig.4 Average forward current Vs. Ambient temperature

HRU0203A

Package Dimensions

Unit : mm

